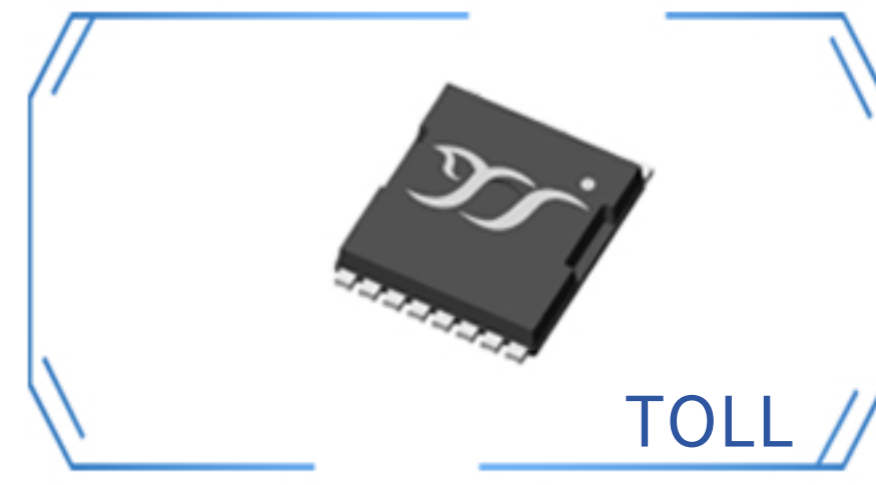
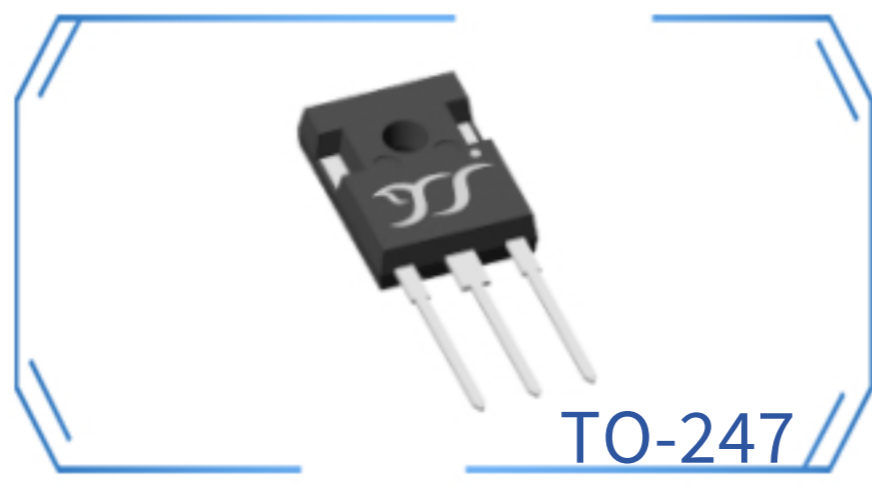


SJ MOSFET for PV Micro-inverter & Industrial /Server Power Supplies

Product Introduction

TO-247 and TOLL encapsulated N600V/650V SJ MOSFETs are manufactured by deep trench technology and multi-layer epitaxy technology, with lower on-state resistance R_{ds} and gate charge Q_g , significantly reducing turn-on and turn-off losses. The products can support higher frequency and dynamic response, which is suitable for applications of high power density and high efficiency power electronic conversion systems.



Product Features

1. Deep trench and multi-layer epitaxy technology is applied, lower internal resistance and excellent switching property;
2. TOLL, TO-247 encapsulation, suitable for high-power applications;
3. Strong UIS capability, better Q_g and R_{ds} parameters, which can support higher frequency and dynamic response.

Electrical Parameters

Product Name	Package	Vds (V)	ID (A)	Vth (V) typ.	Rds10V (mohm) typ.	Rds10V (mohm) max.	Qg10V (nC) typ.	Tj (°C)	N/P
YJN48C60HJ	TO-247	600	33	4	60	72	70	-55-150	N
YJT33C60HJ	TOLL	600	33	4	60	72	70	-55-150	N

Please refer to the official website for more details

Application



PV micro-inverter



Industrial power supply



Server power supply